

# FMP30N60S1

FUJI POWER MOSFET

## Super J-MOS series

## N-Channel enhancement mode power MOSFET

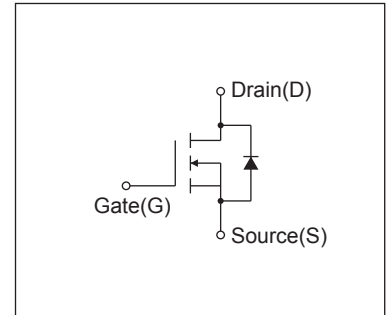
### ■ Features

- Low on-state resistance
- Low switching loss
- easy to use (more controllable switching dV/dt by R<sub>g</sub>)

### ■ Applications

- UPS
- Server
- Telecom
- Power conditioner system
- Power supply

### ■ Equivalent circuit schematic



### ■ Absolute Maximum Ratings at T<sub>c</sub>=25°C (unless otherwise specified)

Description	Symbol	Characteristics	Unit	Remarks
Drain-Source Voltage	V <sub>DS</sub>	600	V	
	V <sub>DSX</sub>	600	V	V <sub>GS</sub> =-30V
Continuous Drain Current	I <sub>D</sub>	±30	A	T <sub>c</sub> =25°C Note*1
		±19	A	T <sub>c</sub> =100°C Note*1
Pulsed Drain Current	I <sub>DP</sub>	±90	A	
Gate-Source Voltage	V <sub>GS</sub>	±30	V	
Repetitive and Non-Repetitive Maximum Avalanche Current	I <sub>AR</sub>	6.6	A	Note *2
Non-Repetitive Maximum Avalanche Energy	E <sub>AS</sub>	849.2	mJ	Note *3
Maximum Drain-Source dV/dt	dV <sub>DS</sub> /dt	50	kV/μs	V <sub>DS</sub> ≤ 600V
Peak Diode Recovery dV/dt	dV/dt	12	kV/μs	Note *4
Peak Diode Recovery -di/dt	-di/dt	100	A/μs	Note *5
Maximum Power Dissipation	P <sub>D</sub>	2.02	W	T <sub>a</sub> =25°C
		250		T <sub>c</sub> =25°C
Operating and Storage Temperature range	T <sub>ch</sub>	150	°C	
	T <sub>stg</sub>	-55 to +150	°C	

Note \*1 : Limited by maximum channel temperature.

Note \*2 : T<sub>ch</sub>≤150°C, See Fig.1 and Fig.2

Note \*3 : Starting T<sub>ch</sub>=25°C, I<sub>AS</sub>=4A, L=97.3mH, V<sub>DD</sub>=60V, R<sub>G</sub>=50Ω, See Fig.1 and Fig.2

E<sub>AS</sub> limited by maximum channel temperature and avalanche current.

Note \*4 : I<sub>F</sub>≤-I<sub>D</sub>, -di/dt=100A/μs, V<sub>DD</sub>≤400V, T<sub>ch</sub>≤150°C.

Note \*5 : I<sub>F</sub>≤-I<sub>D</sub>, dV/dt=12kV/μs, V<sub>DD</sub>≤400V, T<sub>ch</sub>≤150°C.

### ■ Electrical Characteristics at T<sub>c</sub>=25°C (unless otherwise specified)

#### • Static Ratings

Description	Symbol	Conditions	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA V <sub>GS</sub> =0V	600	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	I <sub>D</sub> =250μA V <sub>DS</sub> =V <sub>GS</sub>	2.5	3.0	3.5	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =600V V <sub>GS</sub> =0V	-	-	25	μA
		V <sub>DS</sub> =480V V <sub>GS</sub> =0V	-	-	250	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±30V V <sub>DS</sub> =0V	-	10	100	nA
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> =15A V <sub>GS</sub> =10V	-	0.106	0.125	Ω
Gate resistance	R <sub>G</sub>	f=1MHz, open drain	-	3.2	-	Ω

• Dynamic Ratings

Description	Symbol	Conditions	min.	typ.	max.	Unit
Forward Transconductance	$g_{fs}$	$I_D=15A$ $V_{DS}=25V$	13	26	-	S
Input Capacitance	$C_{iss}$	$V_{DS}=10V$	-	2200	-	pF
Output Capacitance	$C_{oss}$	$V_{GS}=0V$	-	4670	-	
Reverse Transfer Capacitance	$C_{rss}$	$f=1MHz$	-	430	-	
Effective output capacitance, energy related (Note *6)	$C_{o(er)}$	$V_{GS}=0V$ $V_{DS}=0...480V$	-	127	-	
Effective output capacitance, time related (Note *7)	$C_{o(tr)}$	$V_{GS}=0V$ $V_{DS}=0...480V$ $I_D=constant$	-	450	-	
Turn-On Time	$t_{d(on)}$ $t_r$	$V_{DD}=400V, V_{GS}=10V$ $I_D=15A, R_G=13\Omega$ See Fig.3 and Fig.4	-	31	-	ns
Turn-Off Time	$t_{d(off)}$ $t_f$		-	57	-	
Total Gate Charge	$Q_G$	$V_{DD}=480V, I_D=30A$ $V_{GS}=10V$ See Fig.5	-	136	-	
Gate-Source Charge	$Q_{GS}$		-	17	-	
Gate-Drain Charge	$Q_{GD}$		-	73	-	
Drain-Source crossover Charge	$Q_{SW}$		-	18	-	
			-	25	-	nC
			-	11.5	-	

Note \*6 :  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $BV_{DSS}$ .

Note \*7 :  $C_{o(tr)}$  is a fixed capacitance that gives the same charging times as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $BV_{DSS}$ .

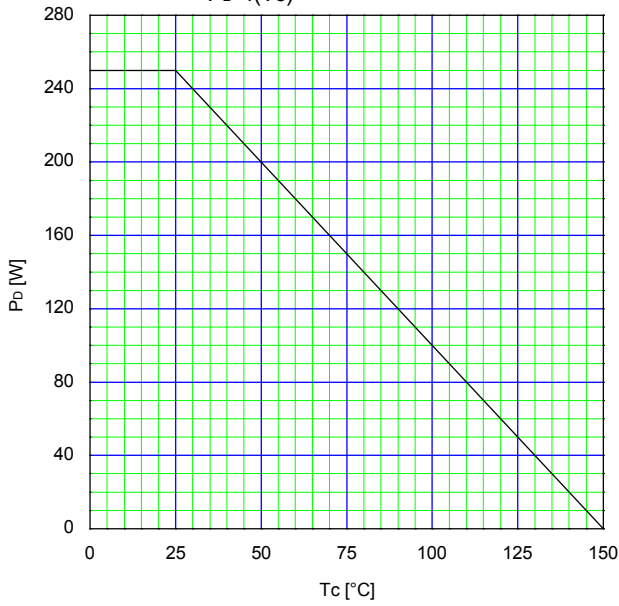
• Reverse Diode

Description	Symbol	Conditions	min.	typ.	max.	Unit
Avalanche Capability	$I_{AV}$	$L=21.7mH, T_{ch}=25^\circ C$ See Fig.1 and Fig.2	6.6	-	-	A
Diode Forward On-Voltage	$V_{SD}$	$I_F=30A, V_{GS}=0V$ $T_{ch}=25^\circ C$	-	0.9	1.35	V
Reverse Recovery Time	$t_{rr}$	$I_F=30A, V_{GS}=0V$ $V_{DD}=400V$ $-di/dt=100A/\mu s$ $T_{ch}=25^\circ C$ See Fig.6	-	430	-	ns
Reverse Recovery Charge	$Q_{rr}$		-	8.6	-	$\mu C$
Peak Reverse Recovery Current	$I_{rp}$		-	38	-	A

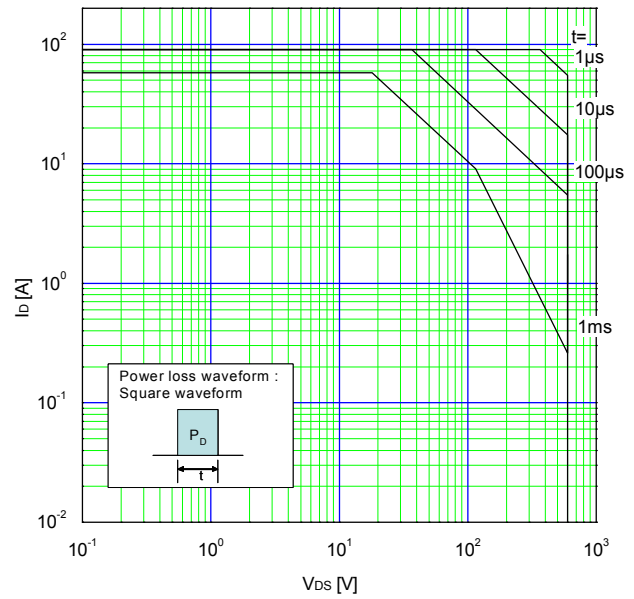
■ Thermal Characteristics

Description	Symbol	min.	typ.	max.	Unit
Channel to Case	$R_{th(ch-c)}$	-	-	0.5	$^\circ C/W$
Channel to Ambient	$R_{th(ch-a)}$	-	-	62	$^\circ C/W$

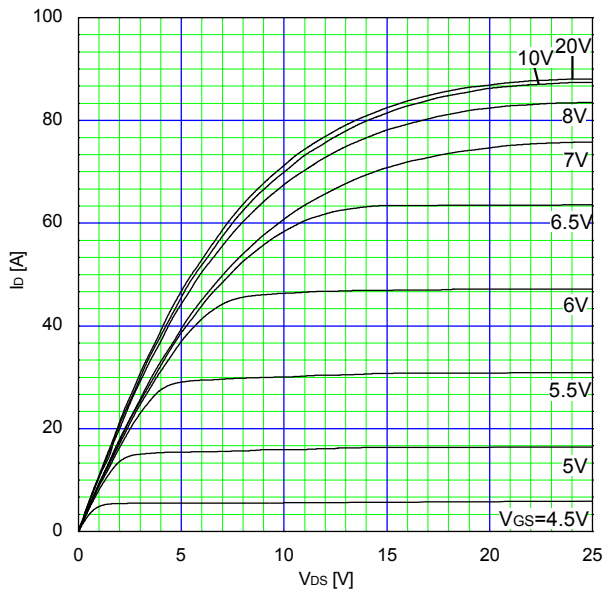
Allowable Power Dissipation  
 $P_D=f(T_c)$



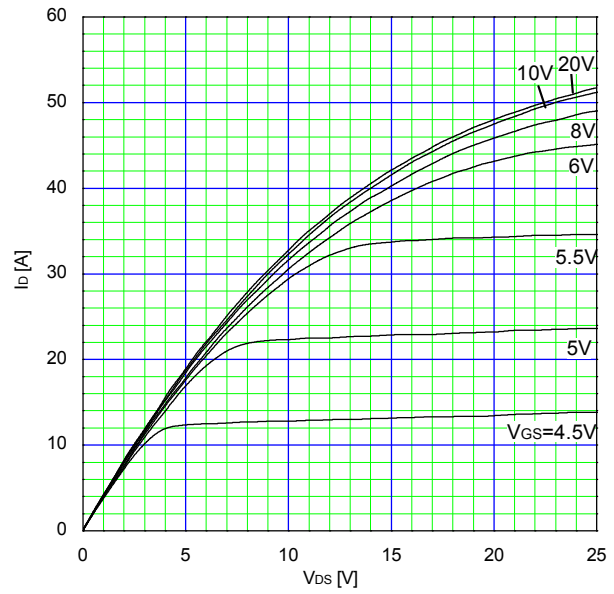
Safe Operating Area  
 $I_D=f(V_{DS}):Duty=0(\text{Single pulse}),T_c=25^\circ\text{C}$



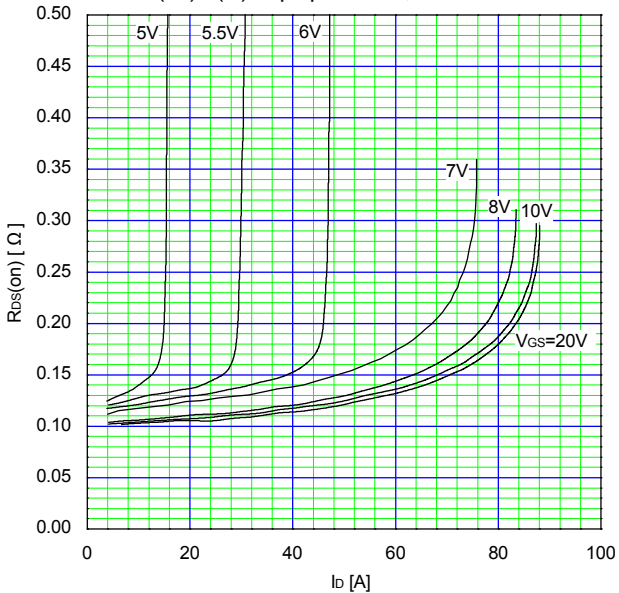
Typical Output Characteristics  
 $I_D=f(V_{DS}):80\mu\text{s pulse test},T_{ch}=25^\circ\text{C}$



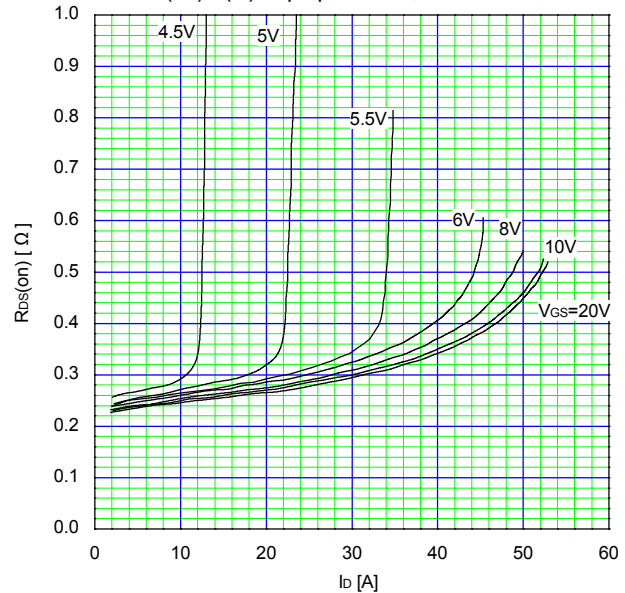
Typical Output Characteristics  
 $I_D=f(V_{DS}):80\mu\text{s pulse test},T_{ch}=150^\circ\text{C}$



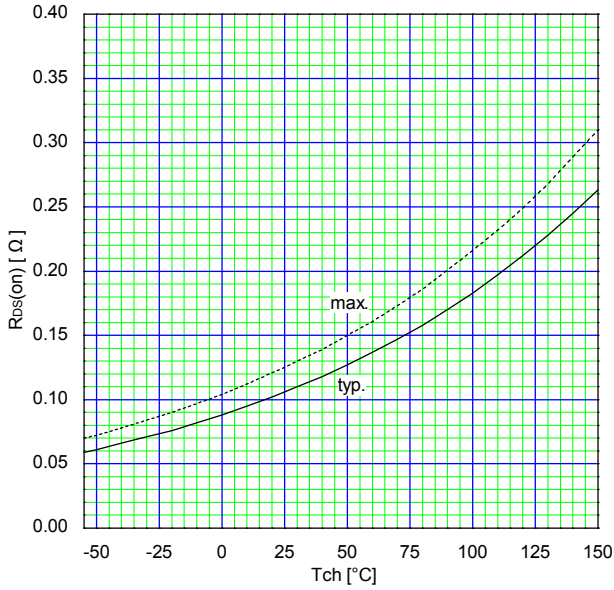
Typical Drain-Source on-state Resistance  
 $R_{DS(on)}=f(I_D):80\mu\text{s pulse test},T_{ch}=25^\circ\text{C}$



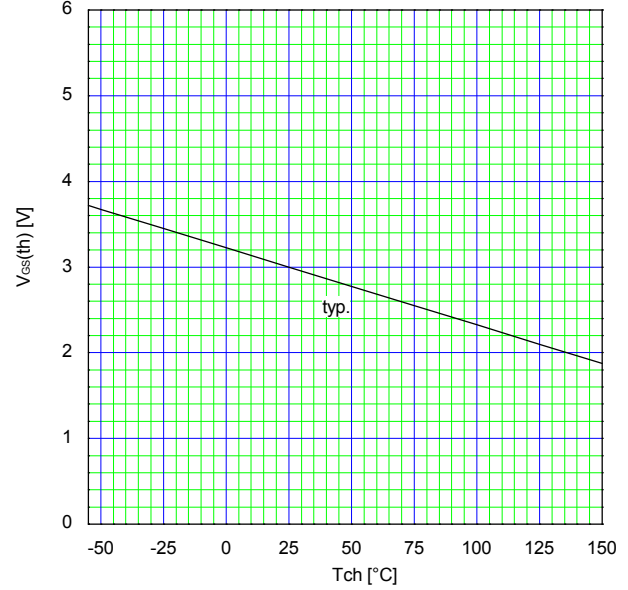
Typical Drain-Source on-state Resistance  
 $R_{DS(on)}=f(I_D):80\mu\text{s pulse test},T_{ch}=150^\circ\text{C}$



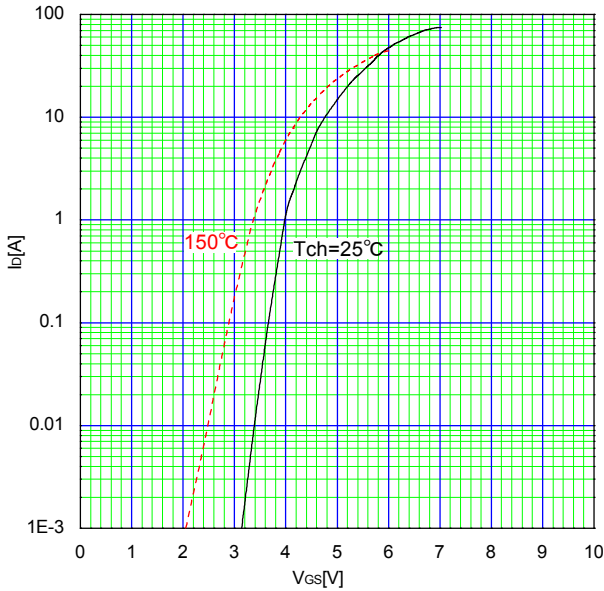
Drain-Source On-state Resistance  
 $R_{DS(on)}=f(T_{ch}):I_D=15A, V_{GS}=10V$



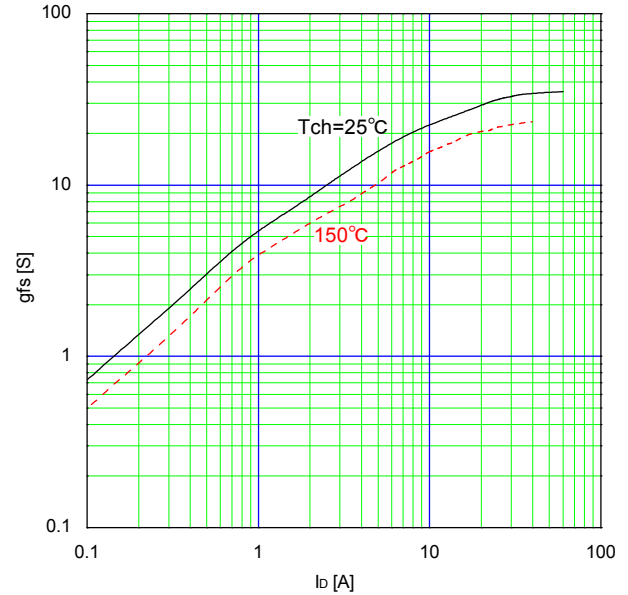
Gate Threshold Voltage vs.  $T_{ch}$   
 $V_{GS(th)}=f(T_{ch}):V_{DS}=V_{GS}, I_D=250\mu A$



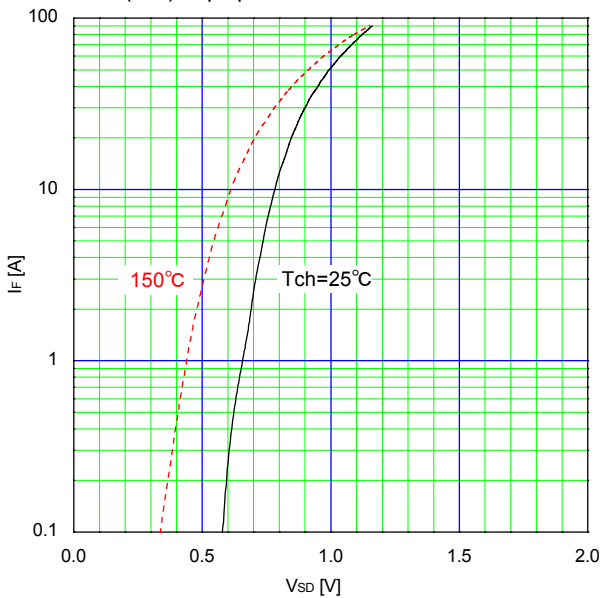
Typical Transfer Characteristic  
 $I_D=f(V_{GS}):80\mu s$  pulse test,  $V_{DS}=25V$



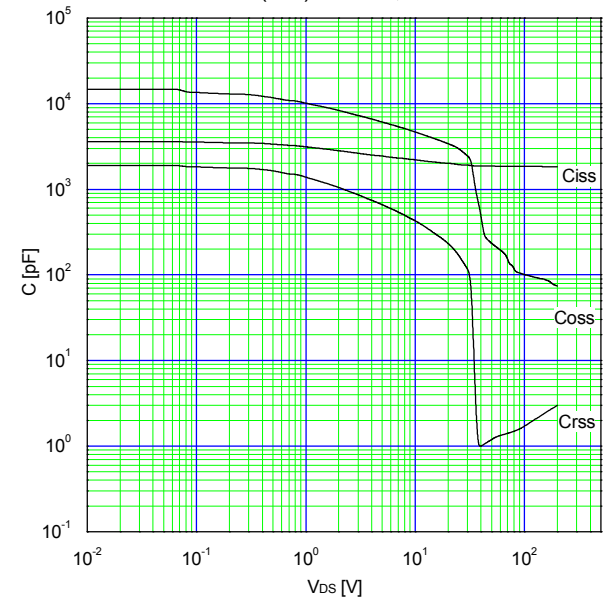
Typical Transconductance  
 $g_{fs}=f(I_D):80\mu s$  pulse test,  $V_{DS}=25V$



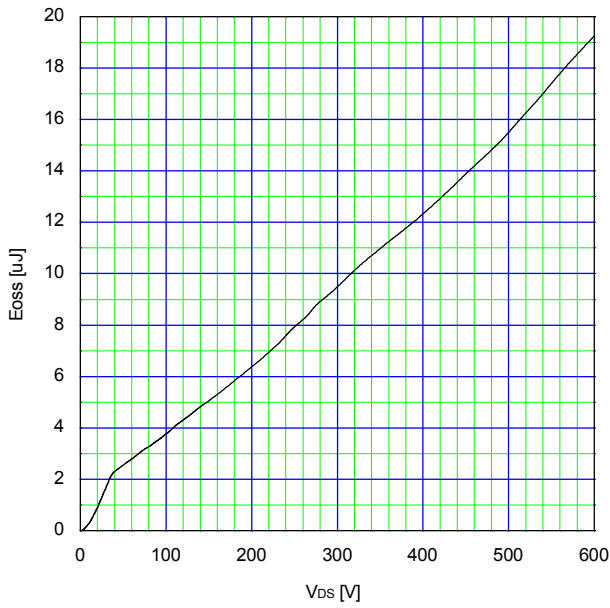
Typical Forward Characteristics of Reverse Diode  
 $I_F=f(V_{SD}):80\mu s$  pulse test



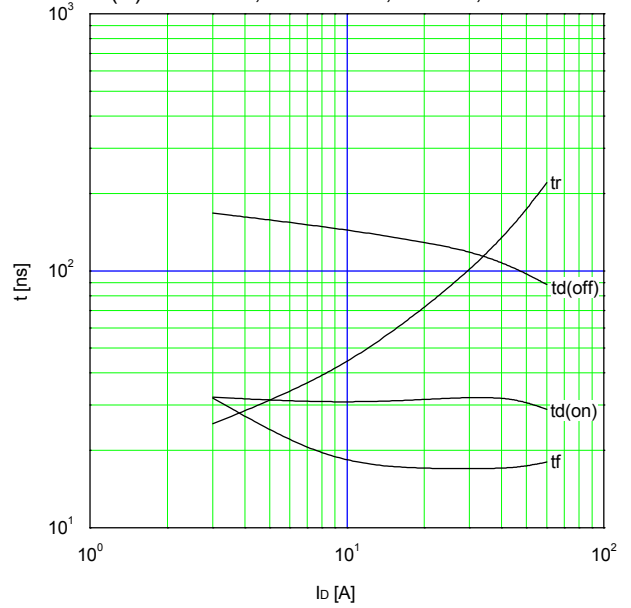
Typical Capacitance  
 $C=f(V_{DS}):V_{GS}=0V, f=1MHz$



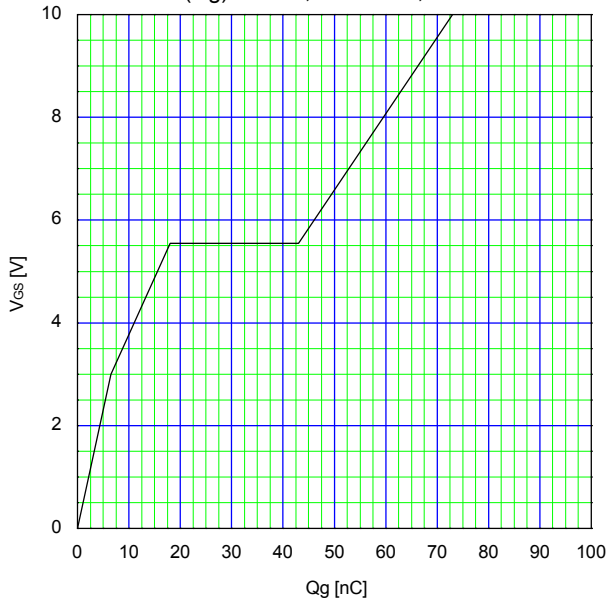
Typical Coss stored energy



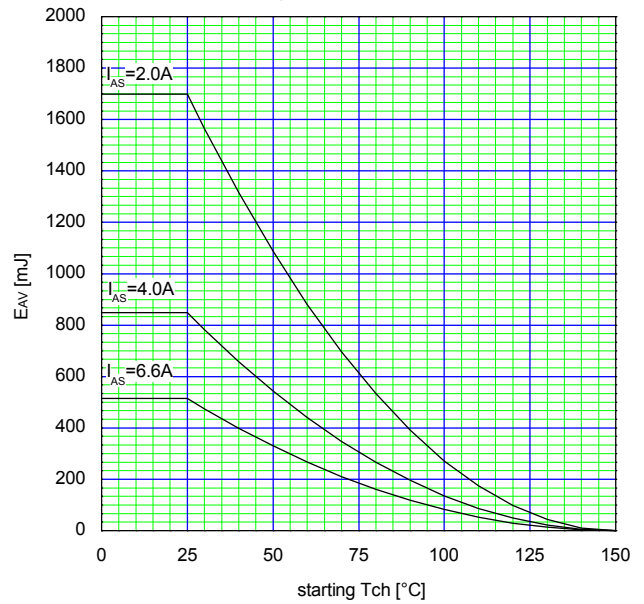
Typical Switching Characteristics vs. ID Tch=25°C  
t=f(ID):Vdd=400V,VGS=10V/0V,RG=13Ω, L=500uH



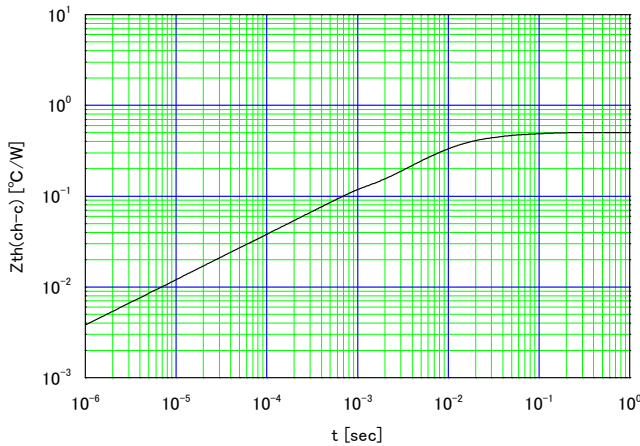
Typical Gate Charge Characteristics  
VGS=f(Qg):ID=30A,Vdd=480V,Tch=25°C



Maximum Avalanche Energy vs. starting Tch  
E(Av)=f(starting Tch):Vcc=60V,I(Av)<=6.6A



Transient Thermal Impedance  
Zth(ch-c)=f(t):D=0



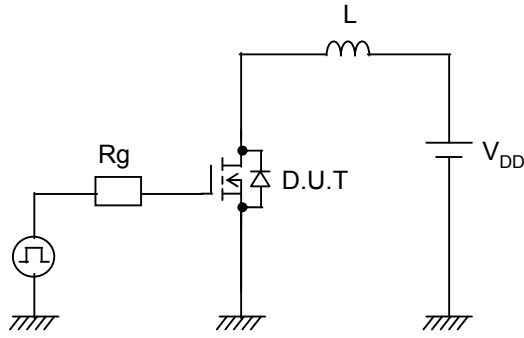


Fig.1 Avalanche Test circuit

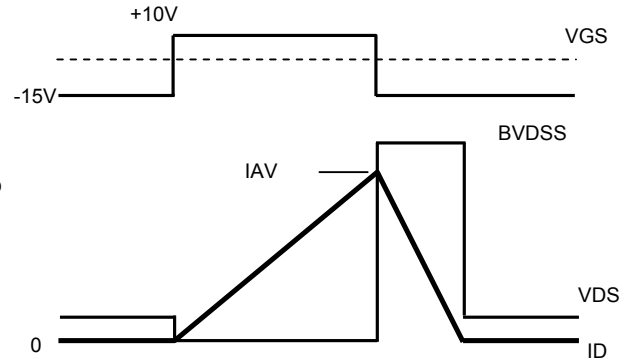


Fig.2 Operating waveforms of Avalanche Test

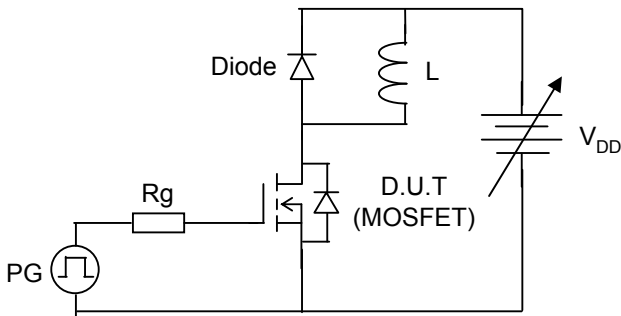


Fig.3 Switching Test circuit

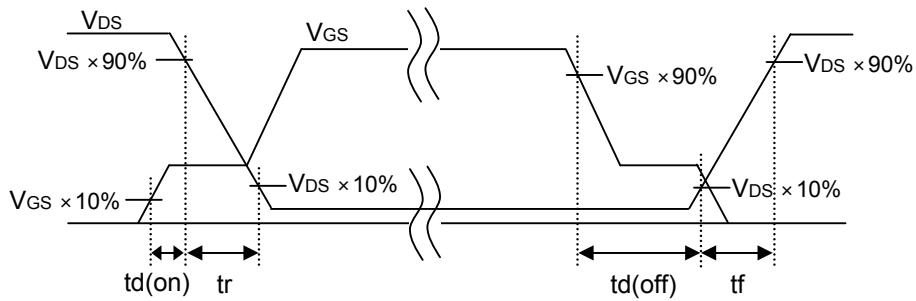


Fig.4 Operating waveform of Switching Test

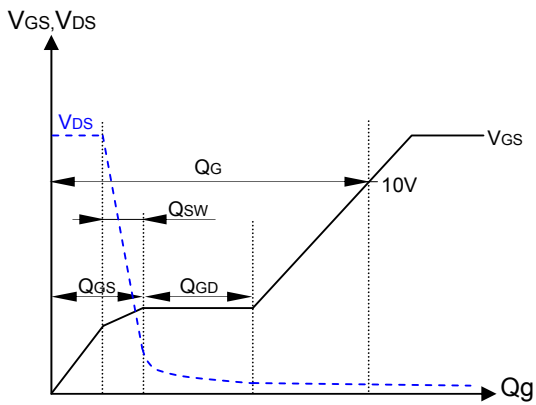


Fig.5 Operating waveform of Gate charge Test

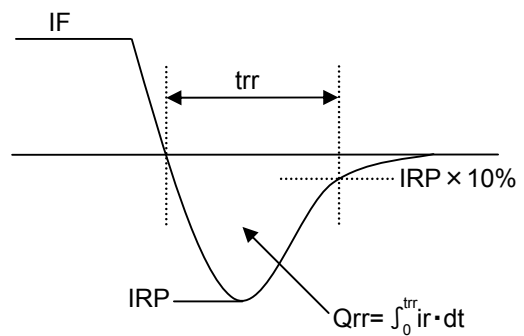
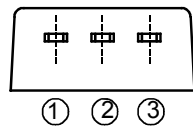


Fig.6 Operating waveform of Body diode Recovery Test

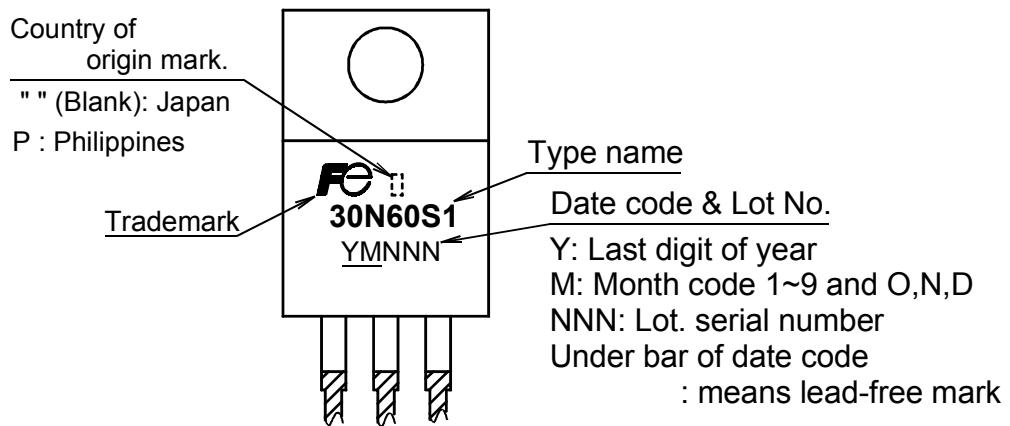


CONNECTION

- ① GATE
- ② DRAIN
- ③ SOURCE

JEDEC : TO-220AB  
DIMENSIONS ARE IN MILLIMETERS.

■ Marking



\* The font (font type,size) and the trademark-size might be actually different.

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